1SS133

SMALL SIGNAL DIODE

VOLTAGE: 90V CURRENT: 130mA

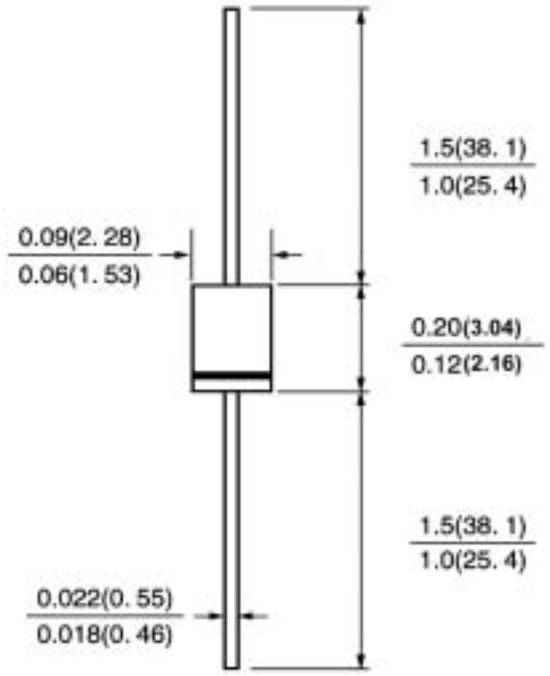
FEATURE

Silicon Single Junction Diode
Fast switching Diode

MECHANICAL DATA

Case: DO-34 Glass case
Polarity: color band denotes cathode
Mounting position: any
Weight: approx . 0.12g

DO-34



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(inductive load rating at 25°C, unless otherwise stated)

Parameter	Symbol	Limit	Units
Recurrent Peak Reverse Voltage	Vrm	90	V
Recurrent Voltage	Vr	80	V
Average Forward Rectified Current Half-Wave Rectification With Resistive Load at Tamp=25°C	If(av)	130	mA
Peak Forward Surge Current T<1.0Ms	Ifsm	600	mA
Power dissipation at tamp=25°C	Ptot	400	mW
Typical Thermal Resistance (Note 1)	R(ja)	350	°C /W
Junction Temperature	Tj	175	°C
Storage Temperature	TS	-65 ~ +175	°C

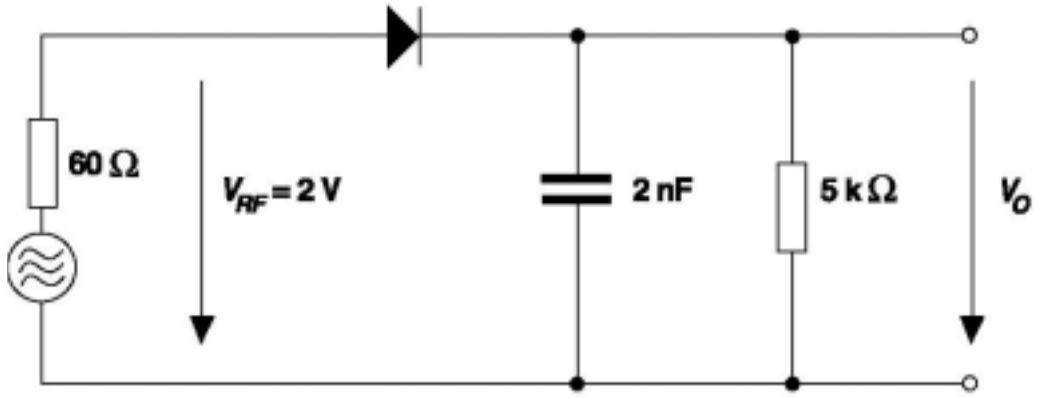
Note:

1. Valid provide that leads at a distance of 8mm from case are kept at ambient temperature

Electrical Characteristics(TJ = 25 ℃ unless otherwise noted)

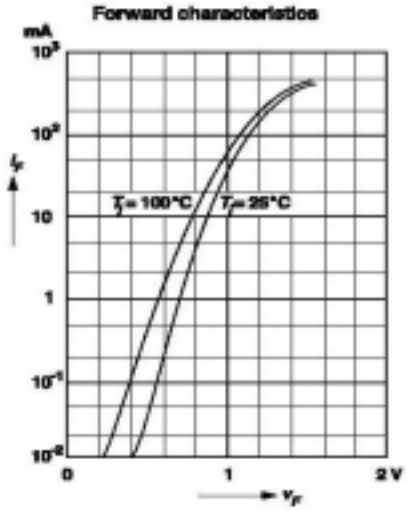
parameter	symbol	Test Condition	min	typ	max	unit
Reverse Breakdown Voltage	Vbr	Ir=100uA	90			V
Forward Voltage	Vf	If=100mA			1.2V	V
Leakage Current	Ir	Vr=80V Vr=20V,Tj=150℃			5.0 50	uA uA
Capacitance	Ctot	Vf=Vr=0V			4	pF
Voltage Rise when Switching ON (tested with 50mA Pulses)	Vfr	Tp=0.1uS,Rise Time<30nS Fp=5 to100KHZ			2.5	nS
Reverse Recovery Time	Trr	If=10mA,Ir=1 mA Vr=6v,Rl=100Ω			4	nS

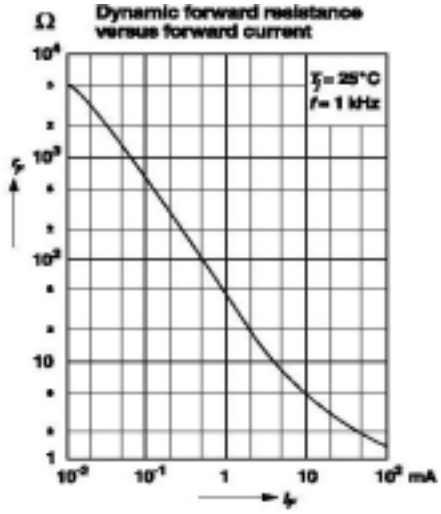
Rectification Efficiency Measurement Circuit

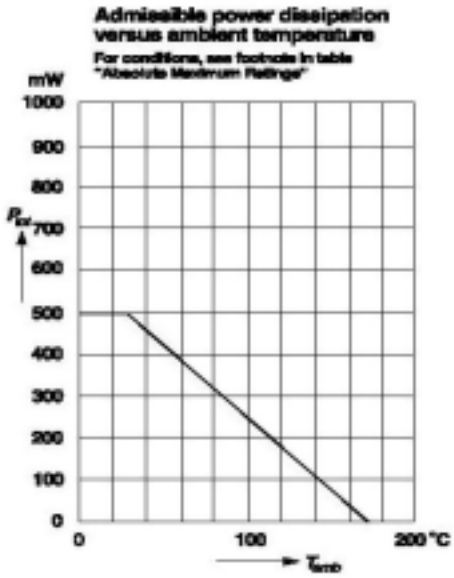


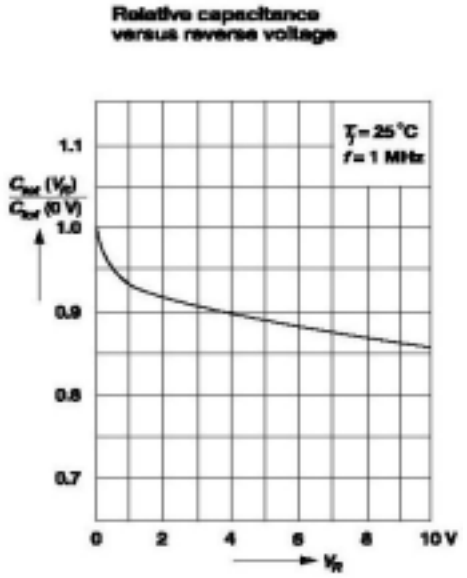
1

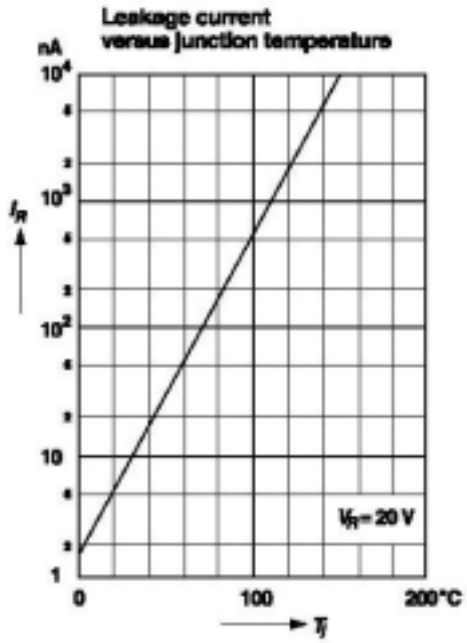
RATINGS AND CHARACTERISTIC CURVES 1SS133

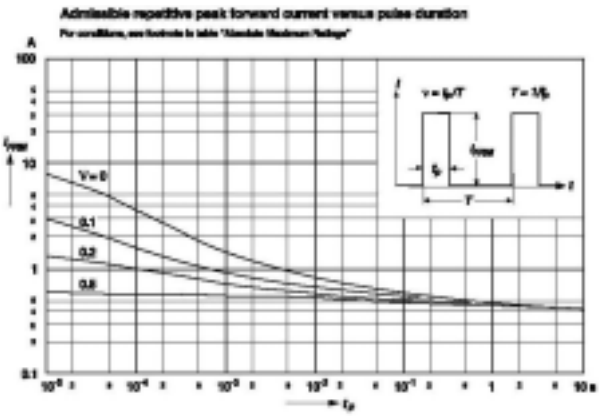












2

Marking：

3